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## **General Description**

Din-Tek IGBTs offer low switching losses, high energy efficiency and high avalanche ruggedness for soft switching application such as IH(induction heating), microwave oven, etc.

#### **FEATURES**

- · High speed switching
- · High system efficiency
- · Soft current turn-off waveforms
- · Extremely enhanced avalanche capability

#### DIM MILLIMETERS A B $4.80 \pm 0.20$ $19.90\pm0.20$ D $2.00 \pm 0.20$ $1.00 \pm 0.20$ $3.00 \pm 0.20$ $3.80 \pm 0.20$ $3.50 \pm 0.20$ $13.90 \pm 0.20$ $12.76 \pm 0.20$ $23.40 \pm 0.20$ 1.5+0.15-0.05 $1.40 \pm 0.20$ $13.60 \pm 0.20$ О $9.60 \pm 0.20$ $5.45 \pm 0.30$ Q $\phi 3.20 \pm 0.10$ $18.70 \pm 0.20$ T 0.60+0.15-0.05 1. GATE 2. COLLECTOR 3. EMITTER TO-3P(N)-E

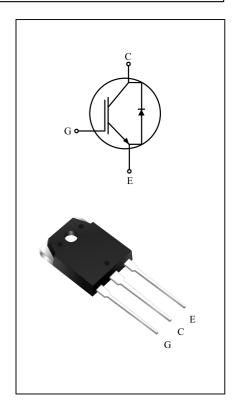
## MAXIMUM RATING (Ta=25 )

CHARACTERISTIC		SYMBOL	RATING	UNIT
Collector-Emitter Voltage		V <sub>CES</sub>	1200	V
Gate-Emitter Voltage		V <sub>GES</sub>	± 20	V
Collector Current	@T <sub>C</sub> =25	$I_{C}$	30	A
Conector Current	@T <sub>C</sub> =100	10	15	A
Pulsed Collector Current		I <sub>CM</sub> *	45	A
Diode Continuous Forward Current	@T <sub>C</sub> =100	I <sub>F</sub> 15		A
Diode Maximum Forward Current		$I_{FM}$	45	A
Maximum Power Dissipation	@T <sub>C</sub> =25	P <sub>D</sub>	190	W
Maximum Fower Dissipation	@T <sub>C</sub> =100	1 D	75	W
Maximum Junction Temperature		T <sub>j</sub>	150	
Storage Temperature Range		$T_{stg}$	-55 to + 150	

<sup>\*</sup>Repetitive rating: Pulse width limited by max. junction temperature

#### THERMAL CHARACTERISTIC

CHARACTERISTIC	SYMBOL	MAX.	UNIT
Thermal Resistance, Junction to Case (IGBT)	$R_{thJC}$	0.82	/W
Thermal Resistance, Junction to Case (DIODE)	R <sub>th JC</sub>	2.3	/W
Thermal Resistance, Junction to Ambient	R <sub>th JA</sub>	40	/W







## **ELECTRICAL CHARACTERISTICS** (Ta=25 )

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Static				•		
Collector-Emitter Breakdown Voltage	BV <sub>CES</sub>	$V_{GE}$ =0V , $I_{C}$ =1.0mA	1200	-	-	V
Collector Cut-off Current	I <sub>CES</sub>	V <sub>GE</sub> =0V, V <sub>CE</sub> =1200V	-	-	1.0	mA
Gate Leakage Current	$I_{GES}$	$V_{CE} = 0V, V_{GE} = \pm 20V$	-	-	± 100	nA
Gate Threshold Voltage	V <sub>GE(th)</sub>	$V_{GE}=V_{CE}$ , $I_{C}=15mA$	4.5	6.0	7.5	V
		$V_{GE} = 15V, I_{C} = 15A$	-	1.85	2.25	V
Collector-Emitter Saturation Voltage	V <sub>CE(sat)</sub>	$V_{GE}$ =15V, $I_{C}$ =15A, $T_{C}$ = 125	-	2.15	-	V
		$V_{GE} = 15V, I_{C} = 30A$	-	2.40	-	V
Dynamic			-			
Total Gate Charge	Qg		-	90	150	nC
Gate-Emitter Charge	$Q_{ge}$	$V_{CC}$ =600V, $V_{GE}$ =15V, $I_{C}$ =15A	-	15	-	nC
Gate-Collector Charge	$Q_{gc}$		-	40	-	nC
Turn-On Delay Time	t <sub>d(on)</sub>		-	30	-	ns
Rise Time	t <sub>r</sub>	$V_{CC}$ =600V, $I_{C}$ =15A, $V_{GE}$ =15V, $R_{G}$ =10 Inductive Load, $T_{C}$ = 25	-	30	-	ns
Turn-Off Delay Time	t <sub>d(off)</sub>		-	150	-	ns
Fall Time	$t_{\mathrm{f}}$		-	150	220	ns
Turn-On Switching Loss	E <sub>on</sub>		-	2.1	-	mJ
Turn-Off Switching Loss	E <sub>off</sub>		-	0.8	-	mJ
Total Switching Loss	E <sub>ts</sub>		-	3.0	-	mJ
Turn-On Delay Time	t <sub>d(on)</sub>		-	35	-	ns
Rise Time	t <sub>r</sub>	$V_{CC}$ =600V, $I_{C}$ =15A, $V_{GE}$ =15V, $R_{G}$ =10 Inductive Load, $T_{C}$ = 125	-	35	-	ns
Turn-Off Delay Time	t <sub>d(off)</sub>		-	180	-	ns
Fall Time	t <sub>f</sub>		-	250	-	ns
Turn-On Switching Loss	E <sub>on</sub>		-	2.5	-	mJ
Turn-Off Switching Loss	E <sub>off</sub>		-	1.7	-	mJ
Total Switching Loss	E <sub>ts</sub>		-	4.5	-	mJ
Input Capacitance	C <sub>ies</sub>		-	1600	-	pF
Ouput Capacitance	C <sub>oes</sub>	V <sub>CE</sub> =30V, V <sub>GE</sub> =0V, f=1MHz	-	60	-	pF
Reverse Transfer Capacitance	C <sub>res</sub>		-	40	-	pF



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## ELECTRICAL CHARACTERISTIC OF DIODE

CHARACTERISTIC	SYMBOL	TEST CONDITION		MIN.	TYP.	MAX.	UNIT
Diode Forward Voltage	$V_{\mathrm{F}}$	$I_F = 15A$	T <sub>C</sub> =25	-	1.8	2.5	- V
			T <sub>C</sub> =125	-	1.9	-	
Diode Reverse Recovery Time	t <sub>rr</sub>		T <sub>C</sub> =25	-	230	300	ns
Diode Reverse Recovery Time		$I_F = 15A$ $di/dt = 200A/ \mu s$	T <sub>C</sub> =125	-	270	-	1115
Diode Peak Reverse Recovery Current	$I_{rr}$		T <sub>C</sub> =25	-	24	31	A
			T <sub>C</sub> =125	-	27	-	A
Diode Reverse Recovery Charge	0		T <sub>C</sub> =25	-	2400	4000	nC
	Q <sub>rr</sub>		T <sub>C</sub> =125	-	3640	1	nc



Fig 1. Saturation Voltage Characteristics

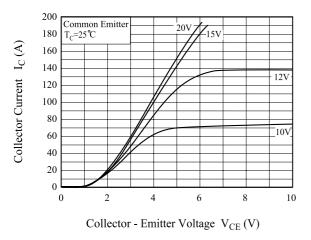


Fig 3. Saturation Voltage vs. Case Temperature

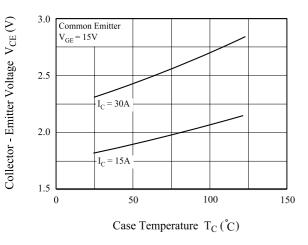


Fig 5. Saturation Voltage vs. V<sub>GE</sub>

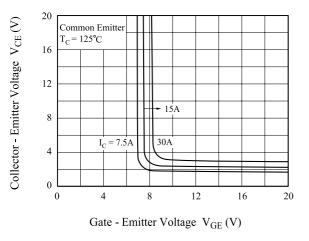


Fig 2. Saturation Voltage Characteristics

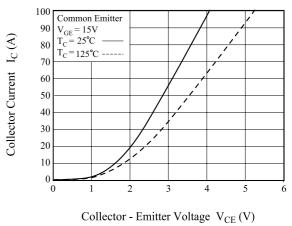


Fig 4. Saturation Voltage vs. V<sub>GE</sub>

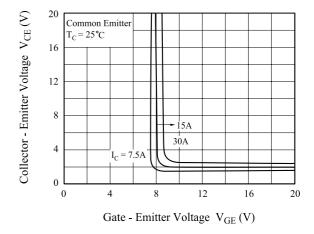
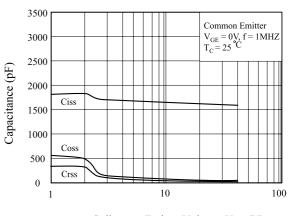


Fig 6. Capacitance Characteristics



Collector - Emitter Voltage  $V_{CE}(V)$ 



Fig 7. Turn-On Characteristics vs. Gate Resistance

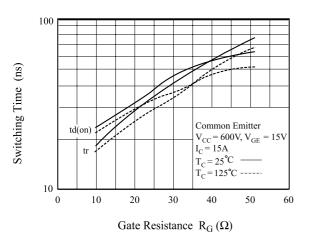


Fig 8. Turn-Off Characteristics vs. Gate Resistance

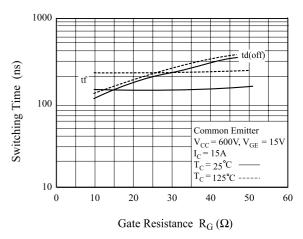


Fig 9. Switching Loss vs. Gate Resistance

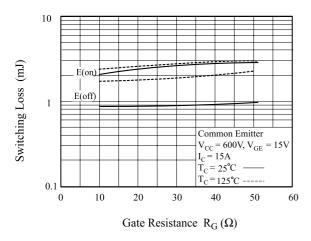


Fig 10. Turn-On Characteristics vs. Collector Current

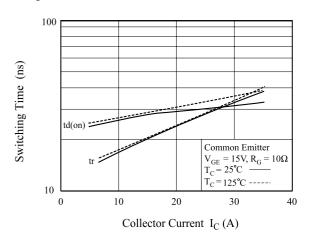


Fig 11. Turn-Off Characteristics vs. Collector Current

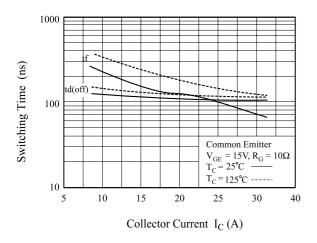


Fig 12. Switching Loss vs. Collector Current

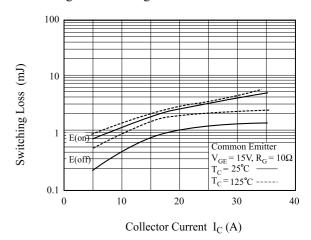




Fig 13. Gate Charge Characteristics

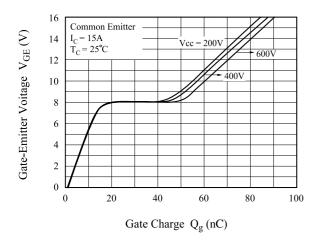


Fig 14. SOA Characteristics

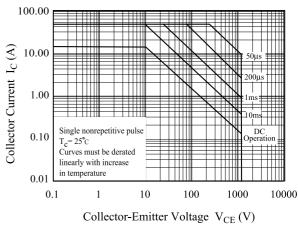


Fig 15. Turn-Off SOA

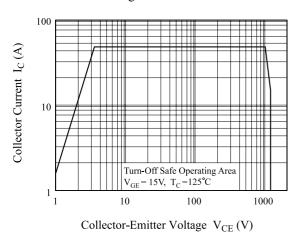
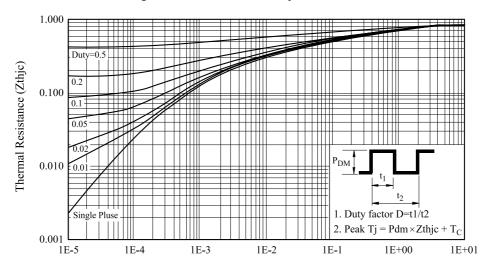


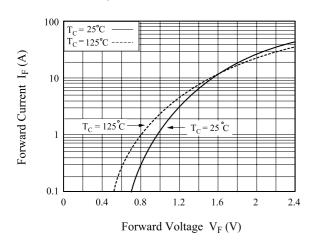
Fig 16. Transient Thermal Impedance of IGBT



Rectangular Pulse Duration (sec)



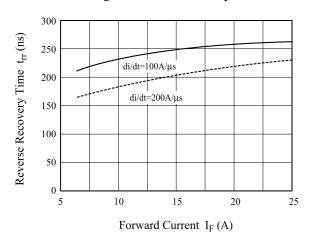
Fig 17. Forward Characteristics



Forward Current  $I_F(A)$ 

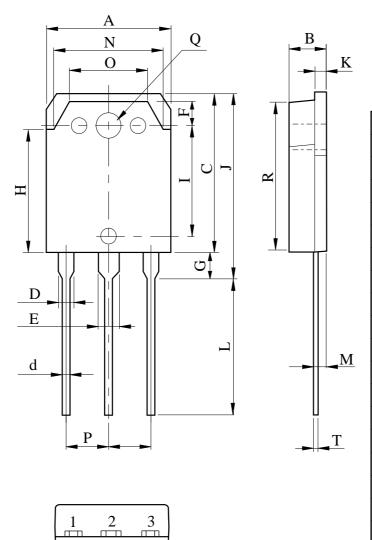
Fig 18. Reverse Recovery Current

Fig 19. Reverse Recovery Time





# **TO-3P (High Voltage)**



DIM	MILLIMETERS
A	$15.60 \pm 0.20$
В	$4.80 \pm 0.20$
С	$19.90 \pm 0.20$
D	$2.00 \pm 0.20$
d	$1.00 \pm 0.20$
Е	$3.00 \pm 0.20$
F	$3.80 \pm 0.20$
G	$3.50 \pm 0.20$
Н	$13.90 \pm 0.20$
I	$12.76 \pm 0.20$
J	$23.40 \pm 0.20$
K	1.5+0.15-0.05
L	$16.50 \pm 0.30$
M	$1.40 \pm 0.20$
О	$9.60 \pm 0.20$
P	$5.45 \pm 0.30$
Q	$\phi 3.20 \pm 0.10$
R	$18.70 \pm 0.20$
Т	0.60+0.15-0.05





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